32K x 9 Bit Static Random Access Memory

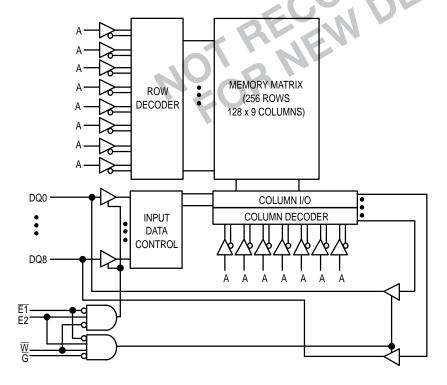
The MCM6705A is a 294,912 bit static random access memory organized as 32,768 words of 9 bits, fabricated using high performance silicon—gate BiCMOS technology. Static design eliminates the need for external clocks or timing strobes.

Output enable (\overline{G}) is a special control feature that provides increased system flexibility and eliminates bus contention problems.

The MCM6705A is available in a 300 mil, 32 lead surface—mount SOJ package.

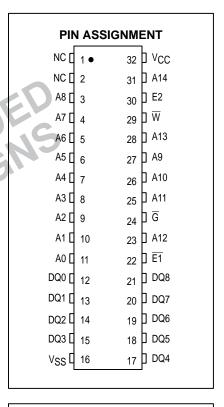
- Single 5.0 V ± 10% Power Supply
- Fully Static No Clock or Timing Strobes Necessary
- All Inputs and Outputs Are TTL Compatible
- Three State Outputs
- Fast Access Times: MCM6705A-10 = 10 ns MCM6705A-12 = 12 ns

BLOCK DIAGRAM



MCM6705A





PIN NAMES						
$\begin{array}{cccc} A0-A14 & Address \\ \overline{W} & Write \ Enable \\ \overline{E1}, E2 & Chip \ Enable \\ \overline{G} & Output \ Enable \\ DQ0-DQ8 & Data \ Input/Output \\ VCC & +5 \ V \ Power \ Supply \\ VSS & Ground \\ NC & No \ Connection \\ \end{array}$						

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TRUTH TABLE (X = Don't Care)

E1	E2	G	W	Mode	V _{CC} Current	Output	Cycle
Н	Χ	Χ	Χ	Not Selected	I _{SB1} , I _{SB2}	High-Z	_
Х	L	Χ	Χ	Not Selected	ISB1, ISB2	High–Z	_
L	Н	Н	Н	Output Disabled	ICCA	High–Z	_
L	Н	L	Н	Read	ICCA	D _{out}	Read Cycle
L	Н	Χ	L	Write	ICCA	High–Z	Write Cycle

ABSOLUTE MAXIMUM RATINGS (See Note)

Rating	Symbol	Value	Unit
Power Supply Voltage	Vcc	- 0.5 to + 7.0	V
Voltage Relative to VSS for Any Pin Except VCC	V _{in} , V _{out}	- 0.5 to V _{CC} + 0.5	V
Output Current	l _{out}	± 30	mA
Power Dissipation	PD	2.0	W
Temperature Under Bias	T _{bias}	- 10 to + 85	°C
Operating Temperature	T _A	0 to + 70	°C
Storage Temperature – Plastic	T _{stg}	- 55 to + 125	°C

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPER-ATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high–impedance circuit.

This BicMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow of at least 500 linear feet per minute is maintained.

DC OPERATING CONDITIONS AND CHARACTERISTICS

(VCC = 5.0 V \pm 10%, TA = 0 to 70°C, Unless Otherwise Noted)

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Тур	Max	Unit
Supply Voltage (Operating Voltage Range)	Vcc	4.5	5.0	5.5	V
Input High Voltage	VIH	2.2		V _{CC} + 0.3*	V
Input Low Voltage	V _{IL}	- 0.5**	_	0.8	٧

 $^{^*}$ V_{IH} (max) = V_{CC} + 0.3 V dc; V_{IH} (max) = V_{CC} + 2.0 V ac (pulse width \leq 2.0 ns) or I \leq 30.0 mA.

DC CHARACTERISTICS

Parameter	Symbol	Min	Max	Unit
Input Leakage Current (All Inputs, V _{in} = 0 to V _{CC})	I _{lkg(I)}	_	± 1.0	μΑ
Output Leakage Current ($\overline{E1} = V_{IH}$ or $E2 = V_{IL}$ or $\overline{G} = V_{IH}$, $V_{out} = 0$ to V_{CC})	I _{lkg(O)}	_	± 1.0	μΑ
Output High Voltage (I _{OH} = - 4.0 mA)	Voн	2.4	_	V
Output Low Voltage (I _{OL} = + 8.0 mA)	VOL	_	0.4	V

POWER SUPPLY CURRENTS

			_	
Parameter	Symbol	MCM6705A-10	MCM6705A-12	Unit
AC Active Supply Current (I _{out} = 0 mA, V _{CC} = max, f = f _{max})	ICCA	195	185	mA
AC Standby Current ($\overline{E1} = V_{IH}$ or $E2 = V_{IL}$, $V_{CC} = max$, $f = f_{max}$)	I _{SB1}	125	120	mA
CMOS Standby Current (V_{CC} = max, f = 0 MHz, $\overline{E1} \ge V_{CC} - 0.2 \text{ V}$, or $E2 \le V_{SS} + 0.2 \text{ V}$, $V_{in} \le V_{SS} + 0.2 \text{ V}$ or $\ge V_{CC} - 0.2 \text{ V}$)	ISB2	55	55	mA

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^{**} V_{IL} (min) = -0.5 V dc @ 30.0 mA; V_{IL} (min) = -2.0 V ac (pulse width \leq 2.0 ns) or $I \leq$ 30.0 mA.

CAPACITANCE (f = 1.0 MHz, dV = 3.0 V, T_A = 25°C, Periodically Sampled Rather Than 100% Tested)

Parameter	Symbol	Max	Unit
Address Input Capacitance	C _{in}	5	pF
Control Pin Input Capacitance (E1, E2, G, W)	C _{in}	6	pF
I/O Capacitance	C _{I/O}	8	pF

AC OPERATING CONDITIONS AND CHARACTERISTICS

(V_{CC} = 5.0 V \pm 10%, T_A = 0 to +70°C, Unless Otherwise Noted)

Input Timing Measurement Reference Level 1.5 V	Output Timing Measurement Reference Level 1.5 V
Input Pulse Levels 0 to 3.0 V	Output Load See Figure 1A
Input Rise/Fall Time	

READ CYCLE (See Notes 1, 2, and 3)

		MCM6705A-10		MCM6705A-12			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Read Cycle Time	^t AVAV	10	_	12	_	ns	4
Address Access Time	^t AVQV	_	10	_	12	ns	
Chip Enable Access Time	^t ELQV	_	10	_	12	ns	
Output Enable Access Time	^t GLQV	_	5	_	6	ns	
Output Hold from Address Change	tAXQX	3	_	3	_	ns	
Chip Enable Low to Output Active	^t ELQX	1	_	1	_	ns	5, 6, 7
Chip Enable High to Output High–Z	^t EHQZ	0	6	0	7	ns	5, 6, 7
Output Enable Low to Output Active	tGLQX	0	_	0	_	ns	5, 6, 7
Output Enable High to Output High–Z	^t GHQZ	0	5	0	6	ns	5, 6, 7

NOTES:

- 1. W is high for read cycle.
- 2. Product sensitivites to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. $\overline{E1}$ is represented by E in this table. E2 would require a transition opposite of $\overline{E1}$.
- 4. All read cycle timing is referenced from the last valid address to the first transitioning address.
- 5. At any given voltage and temperature, tehQZ max < telQX min, and tehQZ max < telQX min, both for a given device and from device
- 6. Transition is measured 200 mV from steady-state voltage with load of Figure 1B.
- 7. This parameter is sampled and not 100% tested.
- 8. Device is continuously selected ($\overline{E1} = V_{IL}$, $E2 = V_{IH}$, $\overline{G} = V_{IL}$).
- 9. Addresses valid prior to or coincident with \overline{E} going low.

AC TEST LOADS

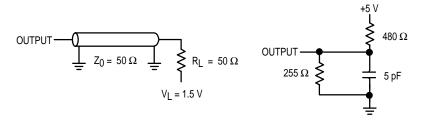


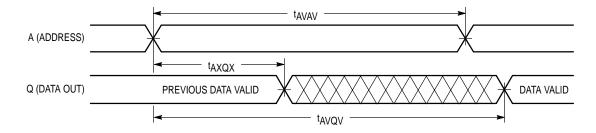
Figure 1A Figure 1B

TIMING LIMITS

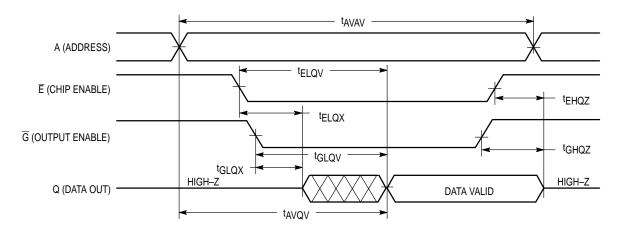
The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. Thus, address setup time is shown as a minimum since the system must supply at least that much time (even though most devices do not require it). On the other hand, responses from the memory are specified from the device point of view. Thus, the access time is shown as a maximum since the device never provides data later than that time.

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READ CYCLE 1 (See Note 8)



READ CYCLE 2 (See Note 9)



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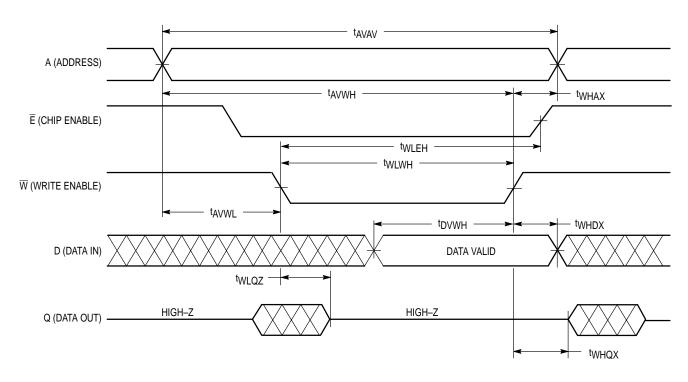
WRITE CYCLE 1 (W Controlled, See Notes 1, 2, and 3)

		MCM6705A-10		MCM6705A-12			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write Cycle Time	^t AVAV	10	_	12	_	ns	4
Address Setup Time	t _{AVWL}	0	_	0	_	ns	
Address Valid to End of Write	^t AVWH	9	_	10	_	ns	
Write Pulse Width	tWLWH, tWLEH	9	_	10	_	ns	
Data Valid to End of Write	^t DVWH	5	_	6	_	ns	
Data Hold Time	tWHDX	0	_	0	_	ns	
Write Low to Data High–Z	tWLQZ	0	5	0	6	ns	5, 6, 7
Write High to Output Active	tWHQX	3	_	3	_	ns	5, 6, 7
Write Recovery Time	tWHAX	0	_	0	_	ns	

NOTES:

- 1. A write occurs during the overlap of \overline{E} low and \overline{W} low.
- 2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. $\overline{E1}$ is represented by E in this table. E2 would require a transition opposite of $\overline{E1}$.
- 4. All write cycle timings are referenced from the last valid address to the first transitioning address.
- 5. Transition is measured 200 mV from steady-state voltage with load of Figure 1B.
- 6. Parameter is sampled and not 100% tested.
- 7. At any given voltage and temperature, tWLQZ max is < tWHQX min both for a given device and from device to device.

WRITE CYCLE 1



MOTOROLA FAST SRAM MCM6705A

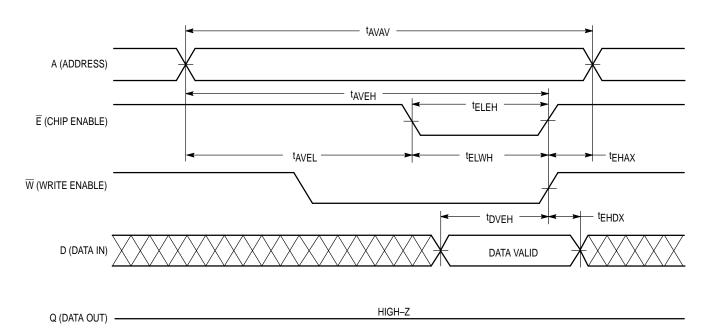
WRITE CYCLE 2 (E Controlled, See Notes 1, 2, and 3)

		MCM6705A-10		MCM6705A-12			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write Cycle Time	t _{AVAV}	10	_	12	_	ns	4
Address Setup Time	^t AVEL	0	_	0	_	ns	
Address Valid to End of Write	^t AVEH	9	_	10	_	ns	
Chip Enable to End of Write	tELWH, tELEH	8	_	9	_	ns	5, 6
Data Valid to End of Write	tDVEH	5	_	6	_	ns	
Data Hold Time	tEHDX	0	_	0	_	ns	
Write Recovery Time	^t EHAX	0	_	0	_	ns	

NOTES:

- 1. A write occurs during the overlap of \overline{E} low and \overline{W} low.
- 2. Product sensitivites to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. $\overline{\text{E1}}$ is represented by E in this table. E2 would require a transition opposite of $\overline{\text{E1}}$.
- 4. All write cycle timing is referenced from the last valid address to the first transitioning address.
- 5. If \overline{E} goes low coincident with or after \overline{W} goes low, the output will remain in a high impedance condition.
- 6. If \overline{E} goes high coincident with or before \overline{W} goes high, the output will remain in a high impedance condition.

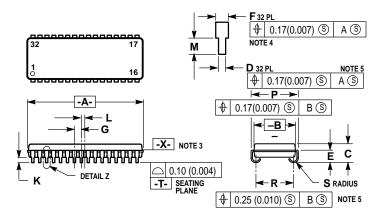
WRITE CYCLE 2



MOTOROLA FAST SRAM MCM6705A

PACKAGE DIMENSIONS

J PACKAGE 300 MIL SOJ **CASE 857-02**

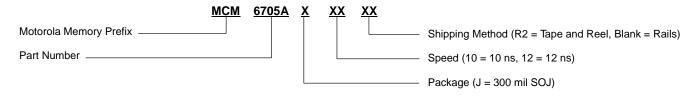


NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- DATUM PLANE –X– LOCATED AT TOP OF MOLD PARTING LINE AND COINCIDENT WITH TOP OF LEAD, WHERE LEAD EXITS BODY.
 TO BE DETERMINED AT PLANE -X-
- TO BE DETERMINED AT PLANE -1
- DIMENSION A & B DO NOT INCLUDE MOLD PROTRUSION. MOLD PROTRUSION SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- 7. 857–01 IS OBSOLETE, NEW STANDARD 857–02.

	MILLIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	20.83	21.08	0.820	0.830
В	7.50	7.74	0.295	0.305
С	3.26	3.75	0.128	0.148
D	0.41	0.50	0.016	0.020
E	2.24	2.48	0.088	0.098
F	0.67	0.81	0.026	0.032
G	1.27	BSC	0.050	BSC
K	0.89	1.14	0.035	0.045
L	0.64	BSC	0.02	BSC
N	0.76	1.14	0.030	0.045
Р	8.38	8.64	0.330	0.340
R	6.60	6.86	0.260 0.270	
S	0.77	1.01	0.030	0.040

ORDERING INFORMATION (Order by Full Part Number)



Full Part Numbers — MCM6705AJ10 MCM6705AJ10R2 MCM6705AJ12 MCM6705AJ12R2

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